

TLV760 100mA 30V 固定输出线性电压调整器

1 特性

- 高达 30V 的宽输入电压范围
- 高达 100mA 的输出电流
- 提供固定输出电压 3.3V、5V、12V 和 15V 版本
- 运行结温范围为 -40°C 至 $+125^{\circ}\text{C}$
- 接 $0.1\mu\text{F}$ 及以上的陶瓷电容器保持稳定工作
- 有效的热保护和电流限制

2 应用

- 用于开关直流/直流转换器的后置稳压器
- 用于数字和模拟电路的偏置电源
- 家用电器
- 电动工具
- 工厂和楼宇自动化

3 说明

TLV760 是一款集成的线性电压调整器，能够以高达 30V 的输入电压运行。在运行温度范围内，TLV760 可在 100mA 满负载下具有 1.2V 的最大压降。TLV760 的标准封装是 3 引脚 SOT-23 封装。

TLV760 提供 3.3V、5V、12V 和 15V 版本。TLV760 系列的 SOT-23 封装允许器件用于空间受限的应用。TLV760 是 LM78Lxx 系列和类似器件的小尺寸替代产品。

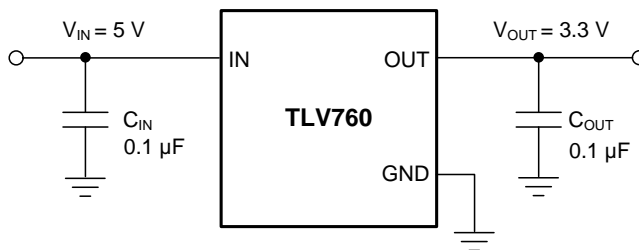
TLV760 用于对遭受高达 30V 的电源瞬态和尖峰的应用（例如电器和自动化应用）中的数字和模拟电路进行偏置。该器件具有可靠的内部热保护功能，可以保护其自身免受由接地短路、环境温度升高、高负载或高压降事件等情况导致的潜在损害。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
TLV760	SOT-23 (3)	2.92mm x 1.30mm

(1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。

典型应用电路



Copyright © 2017, Texas Instruments Incorporated



目录

<p>1 特性 1</p> <p>2 应用 1</p> <p>3 说明 1</p> <p>4 修订历史记录 2</p> <p>5 Pin Configuration and Functions 3</p> <p>6 Specifications 4</p> <p> 6.1 Absolute Maximum Ratings 4</p> <p> 6.2 ESD Ratings 4</p> <p> 6.3 Recommended Operating Conditions 4</p> <p> 6.4 Thermal Information 4</p> <p> 6.5 Electrical Characteristics 5</p> <p> 6.6 Typical Characteristics 6</p> <p>7 Detailed Description 9</p> <p> 7.1 Overview 9</p> <p> 7.2 Functional Block Diagram 9</p> <p> 7.3 Feature Description 9</p>	<p> 7.4 Device Functional Modes 10</p> <p>8 Application and Implementation 11</p> <p> 8.1 Application Information 11</p> <p> 8.2 Typical Application 12</p> <p>9 Power Supply Recommendations 14</p> <p>10 Layout 14</p> <p> 10.1 Layout Guidelines 14</p> <p> 10.2 Layout Example 14</p> <p>11 器件和文档支持 15</p> <p> 11.1 器件支持 15</p> <p> 11.2 接收文档更新通知 15</p> <p> 11.3 社区资源 15</p> <p> 11.4 商标 15</p> <p> 11.5 静电放电警告 15</p> <p> 11.6 Glossary 15</p> <p>12 机械、封装和可订购信息 15</p>
---	---

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

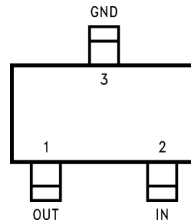
Changes from Original (June 2017) to Revision A

Page

<ul style="list-style-type: none"> • Changed description of pin 1 to "OUT" and pin 2 to "IN" to correct error 3 	3
--	---

5 Pin Configuration and Functions

DBZ Package
3-Pin SOT-23
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	OUT	O	Output voltage, a ceramic capacitor greater than or equal to 0.1 μF is need for the stability of the device. ⁽¹⁾
2	IN	I	Input voltage supply — TI recommends a capacitor of value greater than 0.1 μF at the input. ⁽¹⁾
3	GND	—	Common ground

(1) See [External Capacitors](#) for more details.

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

	MIN	MAX	UNIT
Input voltage (IN to GND)	-0.3	35	V
Output Voltage (OUT)		$V_{IN} + 0.3$	V
Output Current		Internally limited ⁽²⁾	mA
Junction temperature	-40	150	°C
Storage temperature, T_{stg}	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings*⁽¹⁾ may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) See *Recommended Operating Conditions* section for more details.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500
			V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Maximum input voltage (IN to GND)		30	V
Output current (I_{OUT})		100	mA
Input and output capacitor (C_{OUT})	0.1		µF
Junction temperature, T_J	-40	125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV760	UNIT
		DBZ (SOT-23)	
		3 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	275.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	92.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	56.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	2.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	55.6	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

Typical and other limits apply for $T_A = T_J = 25^\circ\text{C}$, $V_{\text{OUT(NOM)}} = 3.3\text{ V}, 5\text{ V}, 12\text{ V}, \text{ and } 15\text{ V}$, unless otherwise specified.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OUT}	Output voltage accuracy	$V_{\text{IN}} = V_{\text{OUT(NOM)}} + 1.5\text{ V}$, $1\text{ mA} \leq I_{\text{OUT}} \leq 100\text{ mA}$		-4%		4%	V
		$V_{\text{IN}} = V_{\text{OUT(NOM)}} + 1.5\text{ V}$, $1\text{ mA} \leq I_{\text{OUT}} \leq 100\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$		-5%		5%	
$\Delta V_{(\Delta V_{\text{IN}})}$	Line regulation	$V_{\text{OUT(NOM)}} + 1.5\text{ V} \leq V_{\text{IN}} \leq 30\text{ V}$ $I_{\text{OUT}} = 1\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	$V_{\text{OUT(NOM)}} = 3.3\text{ V}, 5\text{ V}$		10	30	mV
			$V_{\text{OUT(NOM)}} = 12\text{ V}, 15\text{ V}$		14	45	
$\Delta V_{(\Delta I_{\text{OUT}})}$	Load regulation	$V_{\text{IN}} = V_{\text{OUT(NOM)}} + 1.5\text{ V}$, $10\text{ mA} \leq I_{\text{OUT}} \leq 100\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	$V_{\text{OUT(NOM)}} = 3.3\text{ V}, 5\text{ V}$		20	45	mV
			$V_{\text{OUT(NOM)}} = 12\text{ V}, 15\text{ V}$		45	80	
I_{GND}	Ground pin current	$V_{\text{OUT(NOM)}} + 1.5\text{ V} \leq V_{\text{IN}} \leq 30\text{ V}$, no load, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$			2	5	mA
V_{DO}	Dropout voltage	$I_{\text{OUT}} = 10\text{ mA}$			0.7	0.9	V
		$I_{\text{OUT}} = 10\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$				1	
		$I_{\text{OUT}} = 100\text{ mA}$			0.9	1.1	
		$I_{\text{OUT}} = 100\text{ mA}$, $-40^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$				1.2	
T_{SD}	Thermal shutdown temperature				150		$^\circ\text{C}$

6.6 Typical Characteristics

Unless indicated otherwise, $V_{IN} = V_{NOM} + 1.5\text{ V}$, $C_{IN} = 0.1\ \mu\text{F}$, $C_{OUT} = 0.1\ \mu\text{F}$, and $T_A = 25^\circ\text{C}$.

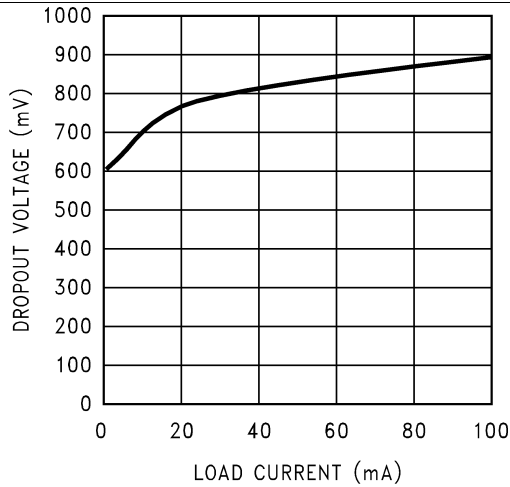


Figure 1. Dropout Voltage vs Load Current

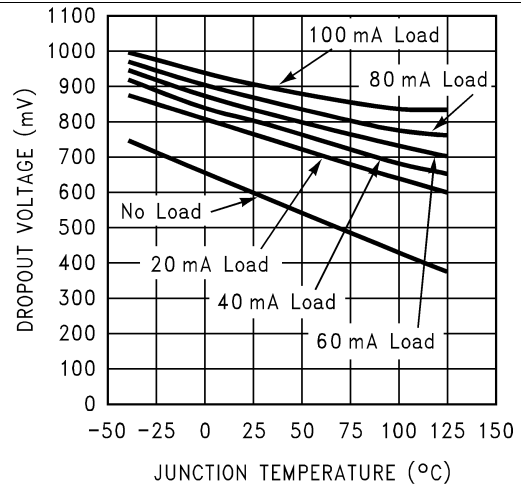


Figure 2. Dropout Voltage vs Junction Temperature

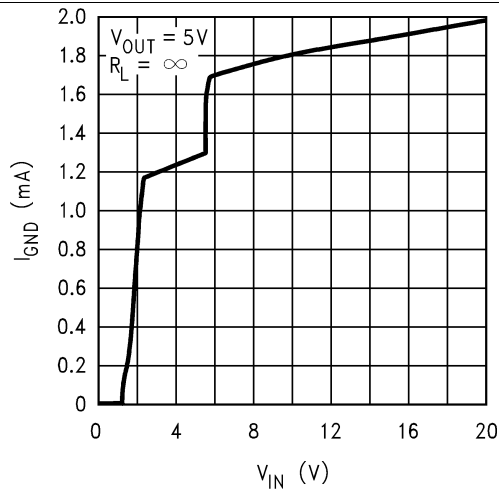


Figure 3. Ground Pin Current vs Input Voltage

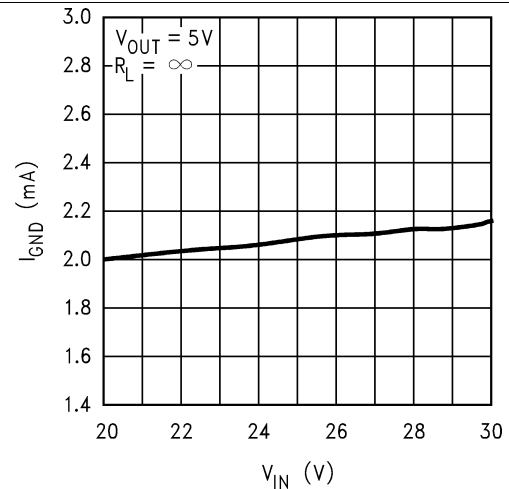


Figure 4. Ground Pin Current vs Input Voltage

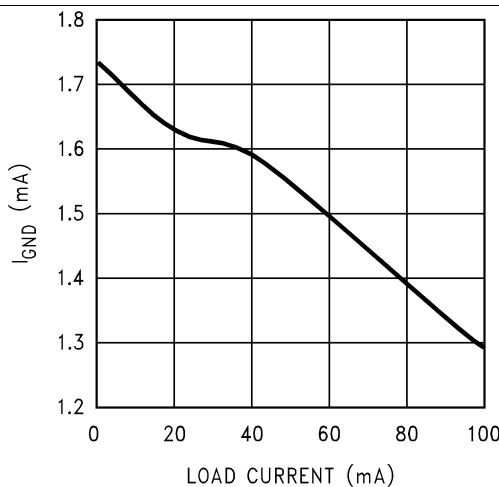


Figure 5. Ground Pin Current vs Load Current

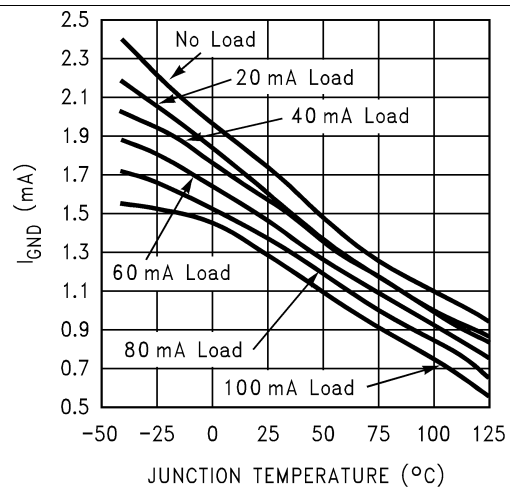


Figure 6. Ground Pin Current vs Junction Temperature

Typical Characteristics (continued)

Unless indicated otherwise, $V_{IN} = V_{NOM} + 1.5\text{ V}$, $C_{IN} = 0.1\ \mu\text{F}$, $C_{OUT} = 0.1\ \mu\text{F}$, and $T_A = 25^\circ\text{C}$.

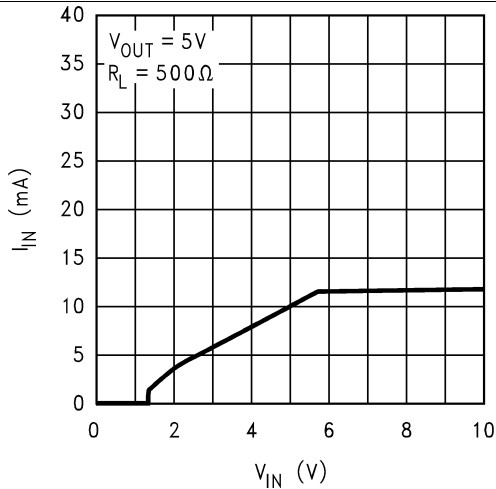


Figure 7. Input Current vs Input Voltage

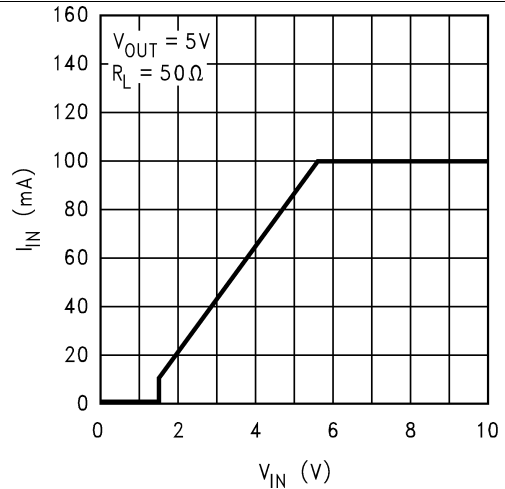


Figure 8. Input Current vs Input Voltage

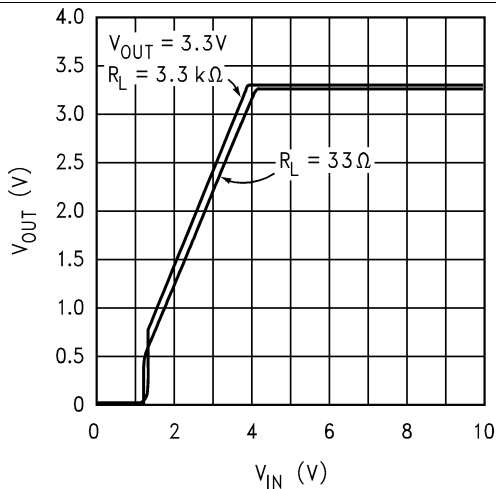


Figure 9. Output Voltage vs Input Voltage

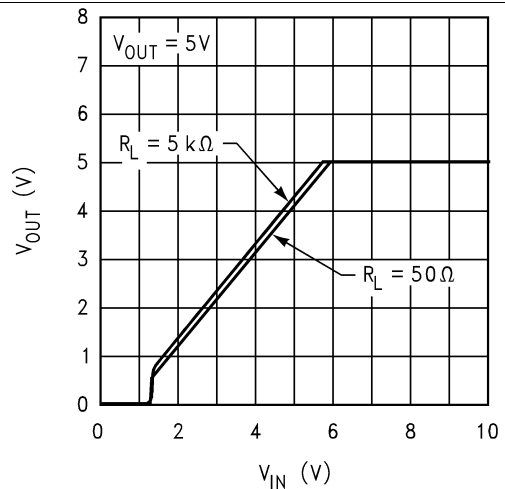


Figure 10. Output Voltage vs Input Voltage

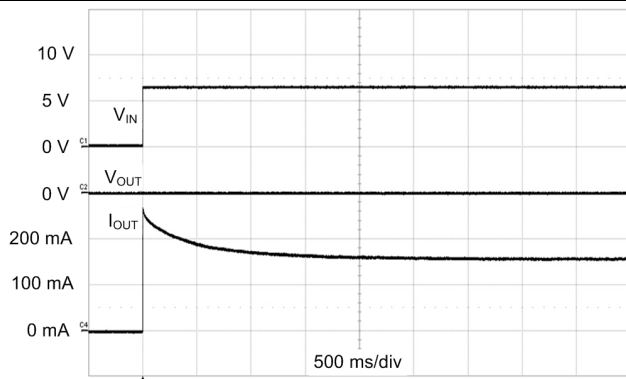


Figure 11. Output Short-Circuit Current

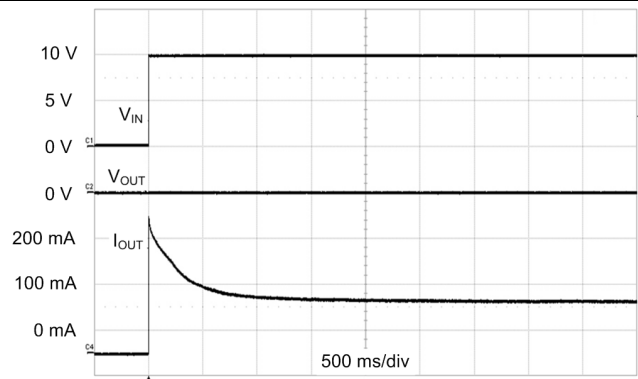


Figure 12. Output Short-Circuit Current

Typical Characteristics (continued)

Unless indicated otherwise, $V_{IN} = V_{NOM} + 1.5\text{ V}$, $C_{IN} = 0.1\ \mu\text{F}$, $C_{OUT} = 0.1\ \mu\text{F}$, and $T_A = 25^\circ\text{C}$.

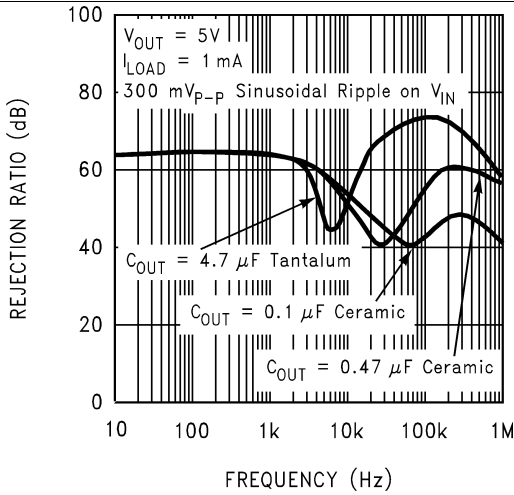


Figure 13. Power Supply Rejection Ratio

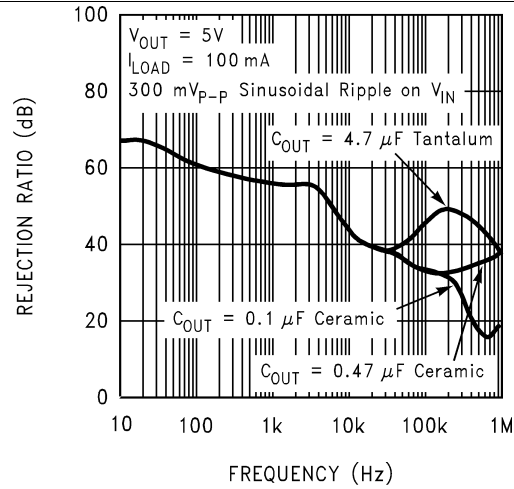


Figure 14. Power Supply Rejection Ratio

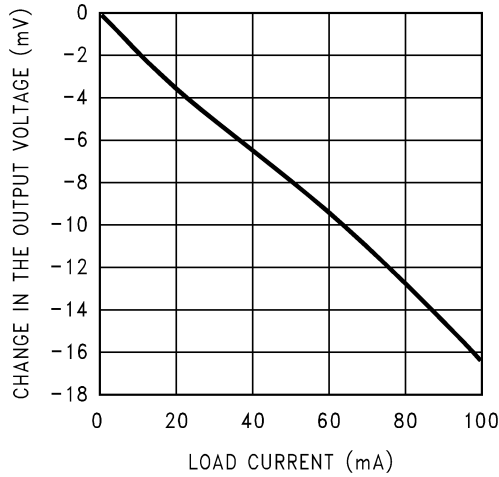


Figure 15. DC Load Regulation

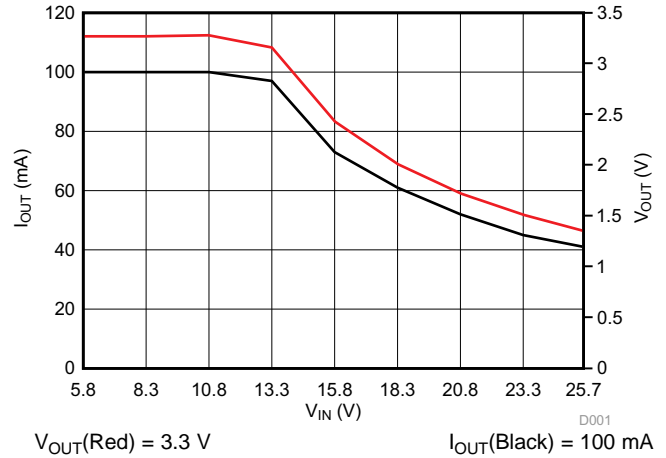


Figure 16. Output Current vs Input Voltage

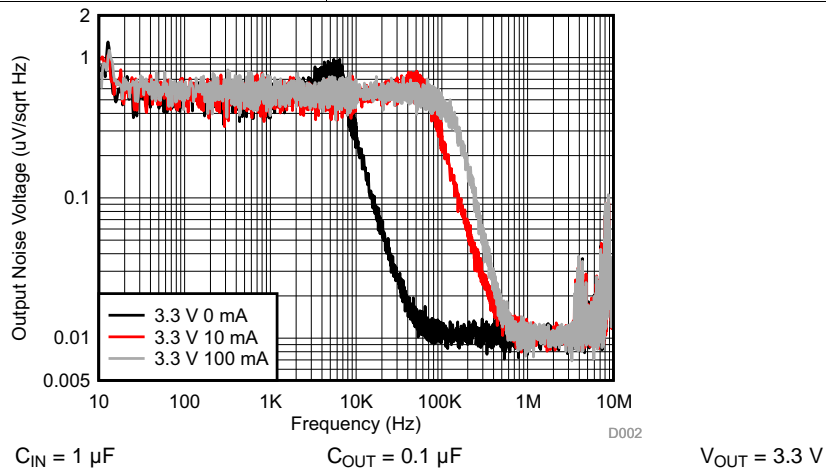


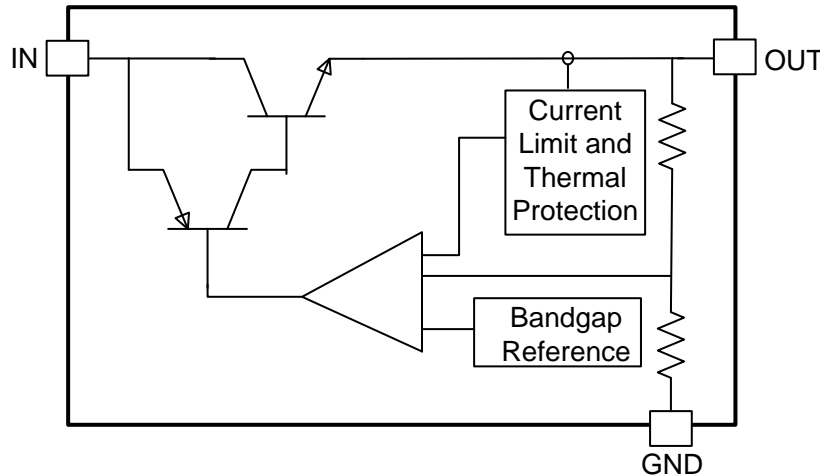
Figure 17. Output Spectral Noise Density vs Frequency

7 Detailed Description

7.1 Overview

The TLV760 is an integrated linear-voltage regulator with inputs that can be as high as 30 V. The TLV760 features [quasi LDO architecture](#), which allows the usage of low ESR capacitors at the output. A ceramic capacitor with a capacitance value greater than or equal to 0.1 μF is adequate to keep the linear regulator in stable operation. The device has a rugged active junction thermal protection mechanism.

7.2 Functional Block Diagram



Copyright © 2017, Texas Instruments Incorporated

7.3 Feature Description

7.3.1 Thermal Protection

The TLV760 contains an active thermal protection mechanism, which limits the junction temperature to 150°C. This protection comes into action when the thermal junction temperature of the device tries to exceed 150°C. The output current of the device is limited or folded back to maintain the junction temperature.

The thermal protection follows [Equation 1](#)

$$P_D = (T_J - T_A) / R_{\theta JA}$$

where

- $P_D = (V_{IN} - V_{OUT}) I_{OUT}$
 - T_J is the junction temperature
 - $R_{\theta JA}$ is the junction-to-ambient thermal resistance
- (1)

When a high drop out condition occurs resulting in higher power dissipation across the device the output current is limited to maintain a constant junction temperature of 150°C. This rugged feature protects the device from higher power dissipation applications as well as the short to ground at the output.

This internal protection circuitry of TLV760 is intended to protect the devices against thermal overload conditions. The circuitry is not intended to replace proper heat sinking. Continuously running the TLV760 into thermal protection degrades device reliability.

For reliable operation, limit junction temperature to a maximum of 125°C. To estimate the thermal margin in a given layout, increase the ambient temperature until the thermal protection is triggered using worst case load and highest input voltage conditions.

Feature Description (continued)

7.3.2 Dropout Voltage

The TLV760 is a bipolar device with [quasi LDO architecture](#). Being a bipolar device the dropout voltage of the device does not change significantly with output load current. The device has a maximum dropout across temperature of 1.2 V at 100-mA load current, which is a significant improvement over the traditional LM78Lxx devices.

7.4 Device Functional Modes

7.4.1 Normal Operation

The TLV760 operates with an input up to 30 V. Its tiny SOT-23 package and quasi-LDO architecture makes it suitable for providing a very tiny 100-mA bias supply. The device regulates to the nominal output voltage when all of the following conditions are met.

- The input voltage is greater than the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)} + V_{DO}$).
- The output current is less than or equal to 100 mA.
- The device junction temperature is less than the thermal protection temperature of 150°C.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TLV760 is a fixed output device which need only input and output capacitors to function. This section discusses the key aspects to implement this linear regulator in typical applications.

8.1.1 Fixed Output

TLV760 comes in fixed output voltage options, 3.3 V, 5 V, 12 V and 15 V. To ensure the proper regulated output, the input voltage should be greater than $V_{OUT(nom)} + V_{DO}$.

8.1.2 External Capacitors

8.1.2.1 Input and Output Capacitor Requirements

A minimum input and output capacitance value of 0.1 μ F is required for stability and adequate transient performance. There is no specific equivalent series resistance (ESR) limitation, although excessively high ESR compromises transient performance. There is no specific limitation on a maximum capacitance value on the input or the output. However while selecting a capacitor, derating factors on the capacitance value should be considered. Use C0G, X7R, or X5R-type ceramic capacitors because these capacitors have minimal variation in capacitance value and ESR over temperature.

8.1.2.2 Load-Step Transient Response

The load-step transient response is the output voltage response by the linear regulator to a step change in load current. The depth of charge depletion immediately after the load step is directly proportional to the amount of output capacitance. However, larger output capacitances decrease any voltage dip or peak occurring during a load step, the control-loop bandwidth is also decreased, thereby slowing the response time. TI recommends to optimally scale output capacitors for a specific application and test for the output load transients.

8.1.3 Power Dissipation

Proper consideration should be given to device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane to ensure the device reliability. The PCB area around the regulator must be as free as possible of other heat-generating devices that cause added thermal stresses. To first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. Power dissipation can be calculated using The thermal protection follows [Equation 1](#):

$$P_D = (T_J - T_A) / R_{\theta JA}$$

where

- $P_D = (V_{IN} - V_{OUT}) I_{OUT}$
 - T_J is the junction temperature
 - $R_{\theta JA}$ is the junction-to-ambient thermal resistance
- (2)

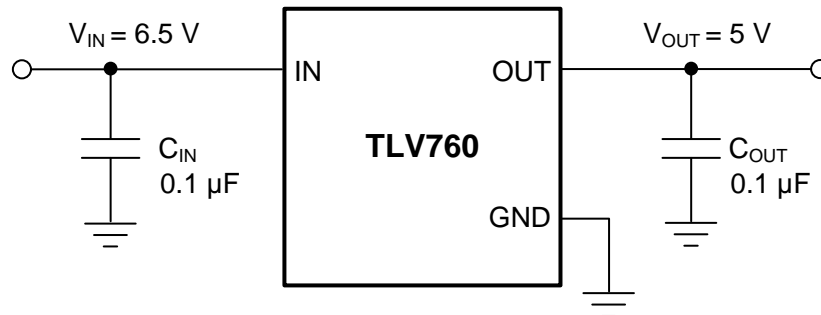
Thus, at a given load current, input and output voltage, maximum power dissipation determines the maximum allowable ambient temperature (T_A) for the device, and vice versa. Power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air (T_A).

$R_{\theta JA}$ is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The $R_{\theta JA}$ recorded in [Thermal Information](#) is determined by the JEDEC standard, PCB, and copper-spreading area and is only used as a relative measure of package thermal performance.

Application Information (continued)

TLV760 integrates a rugged protection where the T_J is limited to 150°C. The maximum power dissipation depends on the ambient temperature and can be calculated using $P_D = (T_J - T_A) / R_{\theta JA}$, for example, substituting the absolute maximum junction temperature, 150°C for T_J , 50°C for T_A , and 275.2 °C/W for $R_{\theta JA}$, the maximum power that can be dissipated is 363 mW. More power can be safely dissipated at lower ambient temperatures. Less power can be safely dissipated at higher ambient temperatures. The power dissipation can be increased by 3.6 mW for each °C below 50°C ambient. It must be derated by 3.6 mW for each °C above 50°C ambient. Proper heat sinking enables the safe dissipation of more power.

8.2 Typical Application



Copyright © 2017, Texas Instruments Incorporated

Figure 18. Typical Application for the 5-V Option

8.2.1 Design Requirements

For typical TLV760 applications, use the parameters in [Table 1](#).

Table 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage	6.5 V
Output voltage	5 V
Output current	100 mA

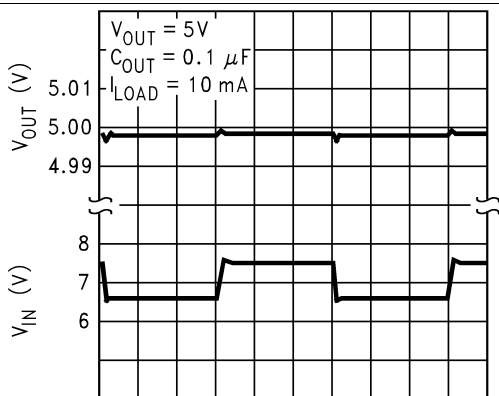
8.2.2 Detailed Design Procedure

The output for TLV76050 is internally set to 5 V. Input and output capacitors can be selected in accordance with the [External Capacitors](#). Ceramic capacitances of 0.1 µF for both input and output are selected.

See the [Layout](#) section for an example of how to PCB layout the TLV760 to achieve best performance.

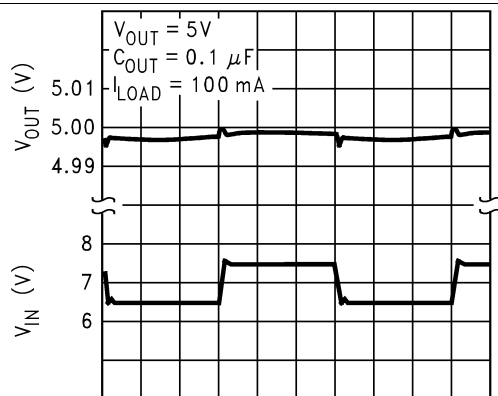
8.2.3 Application Curves

Unless indicated otherwise, $V_{IN} = 6.5\text{ V}$, $V_{OUT} = 5\text{ V}$, $C_{OUT} = 0.1\ \mu\text{F}$, and $T_A = 25^\circ\text{C}$.



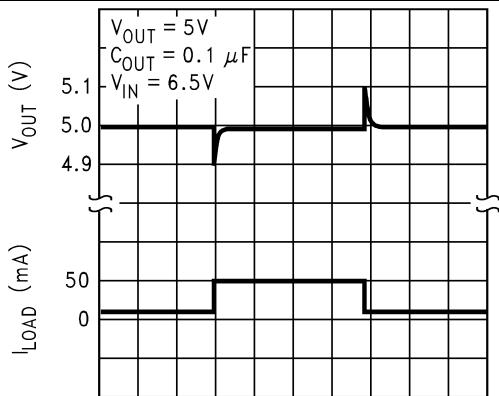
200 $\mu\text{s}/\text{Div}$

Figure 19. Line Transient Response



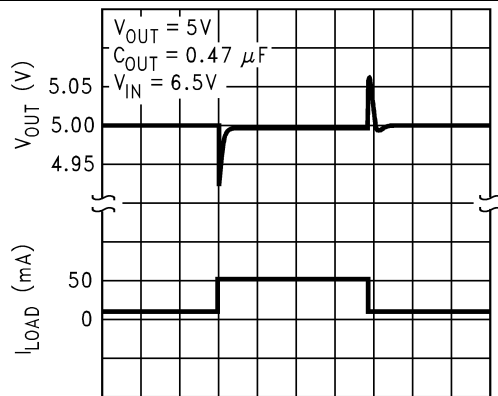
200 $\mu\text{s}/\text{Div}$

Figure 20. Line Transient Response



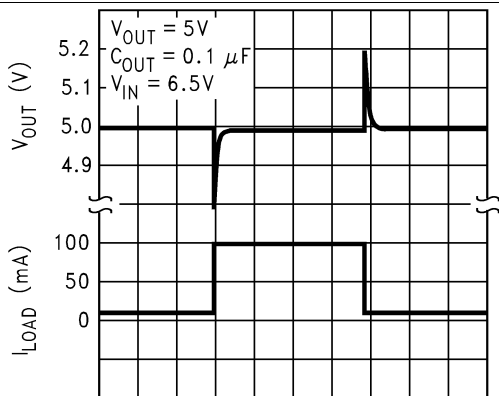
50 $\mu\text{s}/\text{Div}$

Figure 21. Load Transient Response



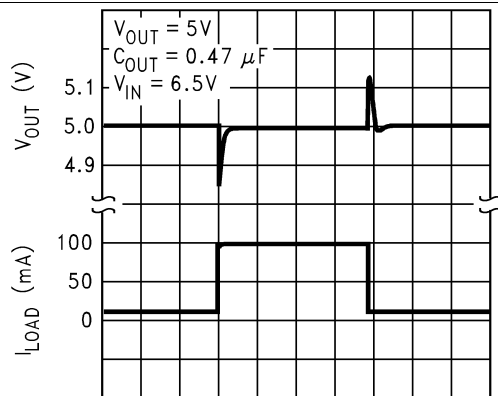
50 $\mu\text{s}/\text{Div}$

Figure 22. Load Transient Response



50 $\mu\text{s}/\text{Div}$

Figure 23. Load Transient Response



50 $\mu\text{s}/\text{Div}$

Figure 24. Load Transient Response

9 Power Supply Recommendations

The TLV760 is designed to operate from input voltage up to 30 V. If the input power supply has ripples, additional input and output capacitors with low ESR can help improve the PSRR at higher frequencies.

10 Layout

10.1 Layout Guidelines

General guidelines for linear regulator designs are to place all circuit components on the same side of the circuit board and as near as practical to the respective TLV760 pin connections. Place ground return connections to the input and output capacitors, and to the TLV760 ground pin as close as possible to each other, connected by a wide, component-side, copper surface. The use of vias and long traces to create TLV760 circuit connections is strongly discouraged and negatively affects system performance.

Use a ground reference plane, either embedded in the PCB itself or located on the bottom side of the PCB opposite the components. This reference plane serves to assure accuracy of the output voltage and to shield noise; it behaves similarly to a thermal plane to spread heat from the linear regulator. In most applications, this ground plane is necessary to meet thermal requirements.

10.2 Layout Example

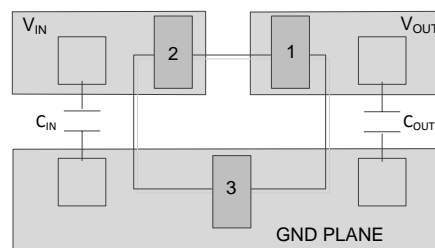


Figure 25. Layout Guideline for TLV760

11 器件和文档支持

11.1 器件支持

11.1.1 相关文档

请参阅如下相关文档：

《[AN-1148 线性稳压器：工作原理和补偿](#)》

11.1.2 Spice 模型

分析模拟电路和系统的性能时，使用 SPICE 模型对电路性能进行计算机仿真非常有用。您可以通过 TLV760 产品文件夹在仿真模型下获取 TLV760 的 SPICE 模型。

11.1.3 器件命名规则

表 2. 订购信息⁽¹⁾

产品	说明
TLV760XXYYZ	XX 是电压符号 YYY 是封装符号。 Z 为封装数量。

(1) 欲获得最新的封装和订货信息，请参阅本文档末尾的封装选项附录，或者访问 www.ti.com 查看器件产品文件夹。

11.2 接收文档更新通知

要接收文档更新通知，请转至 TI.com 上的器件产品文件夹。单击右上角的通知我 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

TI E2E™ 在线社区 *TI 的工程师对工程师 (E2E) 社区*。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 *TI 参考设计支持* 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

11.4 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

11.5 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据如有变更，恕不另行通知和修订此文档。如欲获取此产品说明书的浏览器版本，请参阅左侧的导航。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV76012DBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18G	Samples
TLV76012DBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18G	Samples
TLV76015DBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18C	Samples
TLV76015DBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18C	Samples
TLV76033DBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18H	Samples
TLV76033DBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18H	Samples
TLV76050DBZR	ACTIVE	SOT-23	DBZ	3	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18I	Samples
TLV76050DBZT	ACTIVE	SOT-23	DBZ	3	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	18I	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV76012DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76012DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76015DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76015DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76033DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76033DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76050DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76050DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV76012DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV76012DBZT	SOT-23	DBZ	3	250	210.0	185.0	35.0
TLV76015DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV76015DBZT	SOT-23	DBZ	3	250	210.0	185.0	35.0
TLV76033DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV76033DBZT	SOT-23	DBZ	3	250	210.0	185.0	35.0
TLV76050DBZR	SOT-23	DBZ	3	3000	210.0	185.0	35.0
TLV76050DBZT	SOT-23	DBZ	3	250	210.0	185.0	35.0

GENERIC PACKAGE VIEW

DBZ 3

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4203227/C

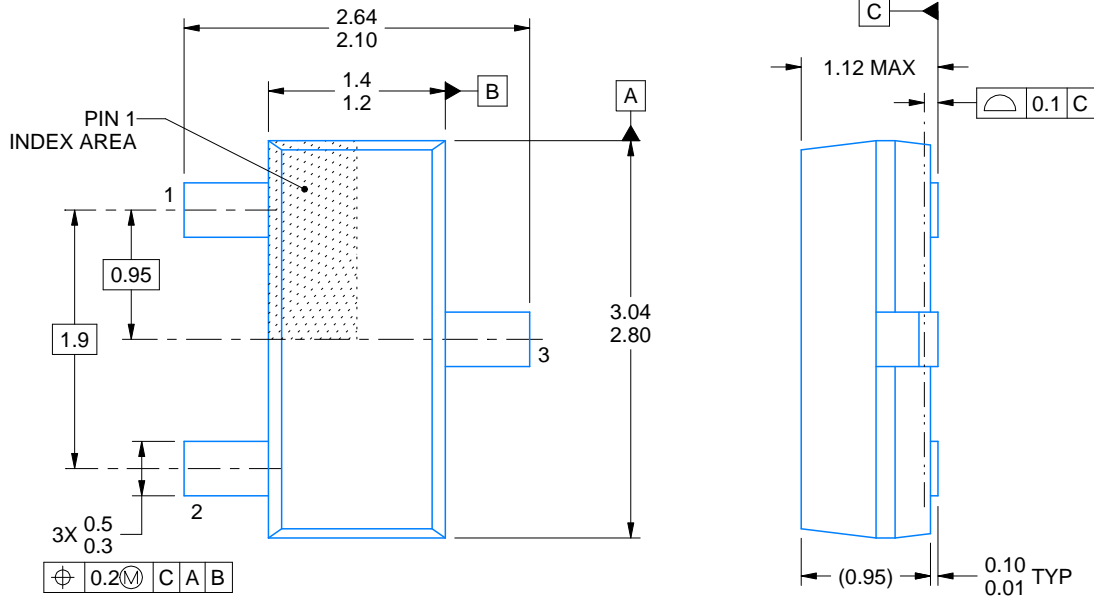
DBZ0003A



PACKAGE OUTLINE

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



4214838/C 04/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-236, except minimum foot length.

EXAMPLE BOARD LAYOUT

DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
SCALE:15X



SOLDER MASK DETAILS

4214838/C 04/2017

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

4214838/C 04/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

重要声明

德州仪器 (TI) 公司有权按照最新发布的 JESD46 对其半导体产品和服务进行纠正、增强、改进和其他修改，并不再按最新发布的 JESD48 提供任何产品和服务。买方在下订单前应获取最新的相关信息，并验证这些信息是否完整且是最新的。

TI 公布的半导体产品销售条款 (<http://www.ti.com/sc/docs/stdterms.htm>) 适用于 TI 已认证和批准上市的已封装集成电路产品的销售。另有其他条款可能适用于其他类型 TI 产品及服务的使用或销售。

复制 TI 数据表上 TI 信息的重要部分时，不得变更该等信息，且必须随附所有相关保证、条件、限制和通知，否则不得复制。TI 对该等复制文件不承担任何责任。第三方信息可能受到其它限制条件的制约。在转售 TI 产品或服务时，如果存在对产品或服务参数的虚假陈述，则会失去相关 TI 产品或服务的明示或暗示保证，且构成不公平的、欺诈性商业行为。TI 对此类虚假陈述不承担任何责任。

买方和在系统中整合 TI 产品的其他开发人员（总称“设计人员”）理解并同意，设计人员在设计应用时应自行实施独立的分析、评价和判断，且应全权负责并确保应用的安全性，及设计人员的应用（包括应用中使用的 TI 产品）应符合所有适用的法律法规及其他相关要求。设计人员就自己设计的应用声明，其具备制订和实施下列保障措施所需的一切必要专业知识，能够 (1) 预见故障的危险后果，(2) 监视故障及其后果，以及 (3) 降低可能导致危险的故障几率并采取适当措施。设计人员同意，在使用或分发包含 TI 产品的任何应用前，将彻底测试该等应用和该等应用中所用 TI 产品的功能。

TI 提供技术、应用或其他设计建议、质量特点、可靠性数据或其他服务或信息，包括但不限于与评估模块有关的参考设计和材料（总称“TI 资源”），旨在帮助设计人员开发整合了 TI 产品的应用，如果设计人员（个人，或如果是代表公司，则为设计人员的公司）以任何方式下载、访问或使用任何特定的 TI 资源，即表示其同意仅为该等目标，按照本通知的条款使用任何特定 TI 资源。

TI 所提供的 TI 资源，并未扩大或以其他方式修改 TI 对 TI 产品的公开适用的质保及质保免责声明；也未导致 TI 承担任何额外的义务或责任。TI 有权对其 TI 资源进行纠正、增强、改进和其他修改。除特定 TI 资源的公开文档中明确列出的测试外，TI 未进行任何其他测试。

设计人员只有在开发包含该等 TI 资源所列 TI 产品的应用时，才被授权使用、复制和修改任何相关 TI 资源。但并未依据禁止反言原则或其他法律授予您任何 TI 知识产权的任何其他明示或默示的许可，也未授予您 TI 或第三方的任何技术或知识产权的许可，该等许可包括但不限于任何专利权、版权、屏蔽作品权或与美国 TI 产品或服务的任何整合、机器制作、流程相关的其他知识产权。涉及或参考了第三方产品或服务的信息不构成使用此类产品或服务的许可或与其相关的保证或认可。使用 TI 资源可能需要您向第三方获得对该等第三方专利或其他知识产权的许可。

TI 资源系“按原样”提供。TI 兹免除对资源及其使用作出所有其他明确或默示的保证或陈述，包括但不限于对准确性或完整性、产权保证、无屡发故障保证，以及适销性、适合特定用途和不侵犯任何第三方知识产权的任何默认保证。TI 不负责任何申索，包括但不限于因组合产品所致或与之有关的申索，也不为或对设计人员进行辩护或赔偿，即使该等产品组合已列于 TI 资源或其他地方。对因 TI 资源或其使用引起或与之有关的任何实际的、直接的、特殊的、附带的、间接的、惩罚性的、偶发的、从属或惩戒性损害赔偿，不管 TI 是否获悉可能会产生上述损害赔偿，TI 概不负责。

除 TI 已明确指出特定产品已达到特定行业标准（例如 ISO/TS 16949 和 ISO 26262）的要求外，TI 不对未达到任何该等行业标准要求而承担任何责任。

如果 TI 明确宣称产品有助于功能安全或符合行业功能安全标准，则该等产品旨在帮助客户设计和创作自己的符合相关功能安全标准和要求的的应用。在应用内使用产品的行为本身不会配有安全特性。设计人员必须确保遵守适用于其应用的相关安全要求和标准。设计人员不可将任何 TI 产品用于关乎性命的医疗设备，除非已由各方获得授权的管理人员签署专门的合同对此类应用专门作出规定。关乎性命的医疗设备是指出现故障会导致严重身体伤害或死亡的医疗设备（例如生命保障设备、心脏起搏器、心脏除颤器、人工心脏泵、神经刺激器以及植入设备）。此类设备包括但不限于，美国食品药品监督管理局认定为 III 类设备的设备，以及在美国以外的其他国家或地区认定为同等类别设备的所有医疗设备。

TI 可能明确指定某些产品具备某些特定资格（例如 Q100、军用级或增强型产品）。设计人员同意，其具备一切必要专业知识，可以为自己的应用选择适合的产品，并且正确选择产品的风险由设计人员承担。设计人员单方面负责遵守与该等选择有关的所有法律或监管要求。

设计人员同意向 TI 及其代表全额赔偿因其不遵守本通知条款和条件而引起的任何损害、费用、损失和/或责任。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122
Copyright © 2017 德州仪器半导体技术（上海）有限公司